

SYSTEM AND METHOD FOR INTEGRATED OXIDE REMOVAL AND
PROCESSING OF A SEMICONDUCTOR WAFER

5 ABSTRACT OF THE DISCLOSURE

 An integrated oxide removal and processing system
(10) includes a process module (30) that may
intentionally add at least one film layer to a single
semiconductor wafer (32). The integrated oxide removal
10 and processing system (10) also includes a transfer
chamber module (20) used to align the semiconductor wafer
(32) for the process module (30). The transfer chamber
module (20) may expose the semiconductor wafer (32) to a
vaporous solution that is inert with respect to the
15 semiconductor wafer (32) and operable to remove an oxide
layer (110) therefrom. More specifically, the
semiconductor wafer (32) includes silicon. In a further
embodiment, the vaporous solution includes HF. In yet a
further embodiment, the vaporous solution includes .049%
20 to 49% HF.